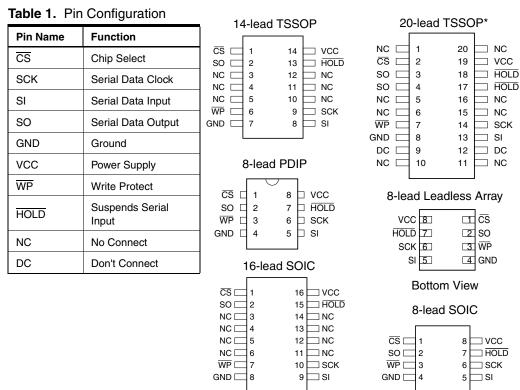
Features

- Serial Peripheral Interface (SPI) Compatible
- Supports SPI Modes 0 (0,0) and 3 (1,1)
- Low-voltage and Standard-voltage Operation
- $-2.7 (V_{CC} = 2.7V \text{ to } 5.5V)$
- 1.8 (V_{CC} = 1.8V to 5.5V)
- 3 MHz Clock Rate
- 64-byte Page Mode and Byte Write Operation
- Block Write Protection
- Protect 1/4, 1/2, or Entire Array
- Write Protect (WP) Pin and Write Disable Instructions for
- Both Hardware and Software Data Protection
- Self-timed Write Cycle (5 ms Typical)
- High-reliability
 - Endurance: 100,000 Write Cycles
 - Data Retention: >200 Years
- Automotive Grade, Extended Temperature and Lead-Free Devices Available
- 8-lead PDIP, 8-lead EIAJ SOIC, 8-lead and 16-lead JEDEC SOIC, 14-lead and 20-lead TSSOP, and 8-lead Leadless Array Packages

Description

The AT25128/256 provides 131,072/262,144 bits of serial electrically-erasable programmable read only memory (EEPROM) organized as 16,384/32,768 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The devices are available in space saving 8-lead PDIP (AT25128/256), 8-lead EIAJ SOIC (AT25128/256), 8-lead and 16-lead JEDEC SOIC (AT25128), 14-lead TSSOP (AT25128), 20-lead TSSOP (AT25128/256), and 8-lead Leadless Array (AT25256) packages. In addition, the entire family is available in 2.7V (2.7V to 5.5V) and 1.8V (1.8V to 5.5V) versions.



*Note: Pins 3, 4 and 17, 18 are internally connected for 14-lead TSSOP socket compatibility.





SPI Serial EEPROMs

128K (16,384 x 8)

256K (32,768 x 8)

AT25128⁽¹⁾ AT25256⁽²⁾

- Notes: 1. This device is not recommended for new designs. Please refer to AT25128A.
 - 2. This device is not recommended for new designs. Please refer to AT25256A.

Rev. 08720-SEEPR-03/05



The AT25128/256 is enabled through the Chip Select pin (\overline{CS}) and accessed via a 3wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate Erase cycle is required before Write.

Block Write protection is enabled by programming the status register with top $\frac{1}{4}$, top $\frac{1}{2}$ or entire array of write protection. Separate Program Enable and Program Disable instructions are provided for additional data protection. Hardware data protection is provided via the \overline{WP} pin to protect against inadvertent write attempts to the status register. The HOLD pin may be used to suspend any serial communication without resetting the serial sequence.

Absolute Maximum Ratings*

Operating Temperature55°C to +125°C	*NOTICE:
Storage Temperature65°C to +150°C	
Voltage on Any Pin with Respect to Ground1.0V to +7.0V	
Maximum Operating Voltage 6.25V	
DC Output Current 5.0 mA	
	Storage Temperature65°C to +150°C Voltage on Any Pin with Respect to Ground1.0V to +7.0V Maximum Operating Voltage

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 1. Block Diagram

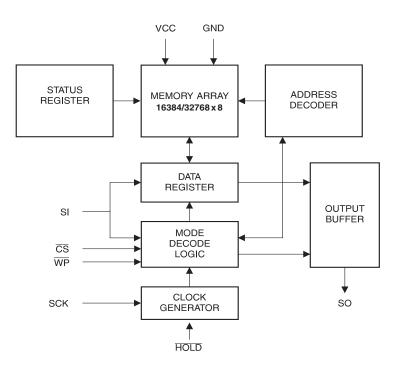


Table 2. Pin Capacitance⁽¹⁾

Symbol	Test Conditions	Max	Units	Conditions
C _{OUT}	Output Capacitance (SO)	8	pF	$V_{OUT} = 0V$
C _{IN}	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

Table 3. DC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.8V$ to +5.5V, $T_{AE} = -40^{\circ}C$ to $+125^{\circ}C$, $V_{CC} = +1.8V$ to +5.5V(unless otherwise noted)

Symbol	Parameter	Test Condition	Test Condition			Max	Units
V _{CC1}	Supply Voltage		1.8		5.5	V	
V _{CC2}	Supply Voltage			2.7		5.5	V
V _{CC3}	Supply Voltage			4.5		5.5	V
I _{CC1}	Supply Current	V _{CC} = 5.0V at 1 MH	z, SO = Open, Read		2.0	3.0	mA
I _{CC2}	Supply Current	V _{CC} = 5.0V at 2 MH SO = Open, Read, V		3.0	5.0	mA	
I _{SB1}	Standby Current	$V_{\rm CC} = 1.8V, \overline{\rm CS} = V_{\rm C}$		0.1	2.0	μA	
I _{SB2}	Standby Current	$V_{CC} = 2.7 V, \overline{CS} = V_{CC}$		0.2	2.0	μA	
I _{SB3}	Standby Current	$V_{CC} = 5.0V, \overline{CS} = V_{CC}$	c		2.0	5.0	μA
I _{IL}	Input Leakage	$V_{IN} = 0V$ to V_{CC}		-3.0		3.0	μA
I _{OL}	Output Leakage	$V_{IN} = 0V$ to V_{CC} , T_{AC}	$c = 0^{\circ}C$ to $70^{\circ}C$	-3.0		3.0	μA
$V_{IL}^{(1)}$	Input Low-voltage			-1.0		V _{CC} x 0.3	V
$V_{IH}^{(1)}$	Input High-voltage			V _{CC} x 0.7		V _{CC} + 0.5	V
V _{OL1}	Output Low-voltage		I _{OL} = 3.0 mA			0.4	V
V _{OH1}	Output High-voltage	$-4.5 \le V_{CC} \le 5.5V$	I _{OH} = -1.6 mA	V _{CC} - 0.8			V
V _{OL2}	Output Low-voltage		l _{OL} = 0.15 mA			0.2	V
V _{OH2}	Output High-voltage	$-1.8V \le V_{CC} \le 3.6V$	I _{OH} = −100 μA	V _{CC} - 0.2			V

Note: 1. V_{IL} and V_{IH} max are reference only and are not tested.





Table 4. AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to $+ 85^{\circ}C$, $T_{AE} = -40^{\circ}C$ to $+125^{\circ}C$, $V_{CC} = As$ Specified, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units
f _{SCK}	SCK Clock Frequency	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	0 0 0	3.0 2.1 0.5	MHz
t _{RI}	Input Rise Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5		2 2 2	μs
t _{FI}	Input Fall Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5		2 2 2	μs
t _{wH}	SCK High Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	150 200 800		ns
t _{WL}	SCK Low Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	150 200 800		ns
t _{cs}	CS High Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	250 250 1000		ns
t _{CSS}	CS Setup Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	100 250 1000		ns
t _{CSH}	CS Hold Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	150 250 1000		ns
t _{SU}	Data In Setup Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	30 50 100		ns
t _H	Data In Hold Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	50 50 100		ns
t _{HD}	Hold Setup Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	100 100 400		ns
t _{CD}	Hold Hold Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	200 300 400		ns
t _v	Output Valid	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	0 0 0	150 200 800	ns
t _{HO}	Output Hold Time	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5	0 0 0		ns
t _{LZ}	Hold to Output Low Z	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	0 0 0	100 200 300	ns

4 AT25128/256

Table 4. AC Characteristics (Continued)

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to + 85°C, $T_{AE} = -40^{\circ}C$ to +125°C, $V_{CC} = As$ Specified,
CL = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Мах	Units
t _{HZ}	Hold to Output High Z	4.5 – 5.5 2.7 – 5.5 1.8 – 5.5		100 200 300	ns
t _{DIS}	Output Disable Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		200 250 1000	ns
t _{wc}	Write Cycle Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		5 10 10	ms
Endurance ⁽¹⁾	5.0V, 25°C, Page Mode		100K		Write Cycles

Note: 1. This parameter is characterized and is not 100% tested. Contact Atmel for further information.

Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the serial clock pin (SCK) is always an input, the AT25128/256 always operates as a slave.

TRANSMITTER/RECEIVER: The AT25128/256 has separate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with \overline{CS} going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25128/256, and the serial output pin (SO) will remain in a high impedance state until the falling edge of \overline{CS} is detected again. This will reinitialize the serial communication.

CHIP SELECT: The AT25128/256 is selected when the \overline{CS} pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

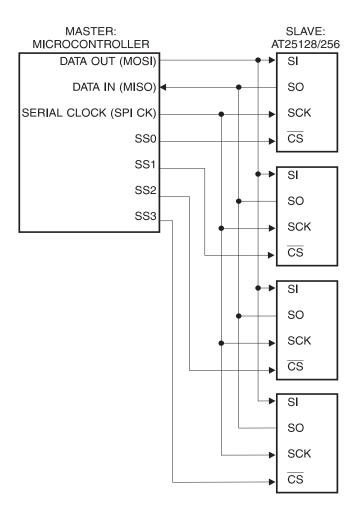
HOLD: The HOLD pin is used in conjunction with the \overline{CS} pin to select the AT25128/256. When the device is selected and a serial sequence is underway, HOLD can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the HOLD pin must be brought low while the SCK pin is low. To resume serial communication, the HOLD pin is brought high while the SCK pin is low (SCK may still toggle during HOLD). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin (\overline{WP}) will allow normal read/write operations when held high. When the \overline{WP} pin is brought low and WPEN bit is "1", all write operations to the status register are inhibited. \overline{WP} going low while \overline{CS} is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, \overline{WP} going low will have no effect on any write operation to the status register. The \overline{WP} pin function is blocked when the WPEN bit in the status register is "0". This will allow the user to install the AT25128/256 in a system with the \overline{WP} pin tied to ground and still be able to write to the status register. All \overline{WP} pin functions are enabled when the WPEN bit is set to "1".





Figure 2. SPI Serial Interface



Functional Description

The AT25128/256 is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6800 type series of microcontrollers.

The AT25128/256 utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in Table 5. All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low \overline{CS} transition.

Table 5. Instruction Set for the AT25128/256

Instruction Name Instruction Forma		Operation
WREN	0000 X110	Set Write Enable Latch
WRDI	0000 X100	Reset Write Enable Latch
RDSR	0000 X101	Read Status Register
WRSR	0000 X001	Write Status Register
READ	0000 X011	Read Data from Memory Array
WRITE	0000 X010	Write Data to Memory Array

WRITE ENABLE (WREN): The device will power-up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the \overline{WP} pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The Ready/Busy and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write Protection bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

Table 6. Status Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
WPEN	Х	Х	Х	BP1	BP0	WEN	RDY

Bit	Definition
Bit 0 (RDY)	Bit $0 = "0" (\overline{RDY})$ indicates the device is READY. Bit $0 = "1"$ indicates the write cycle is in progress.
Bit 1 (WEN)	Bit $1 = "0"$ indicates the device <i>is not</i> WRITE ENABLED. Bit $1 = 1$ indicates the device is WRITE ENABLED.
Bit 2 (BP0)	See Table 8.
Bit 3 (BP1)	See Table 8.
Bits 4 - 6 are "0"s wh	en device is not in an internal write cycle.
Bit 7 (WPEN)	See Table 9.
Bits 0 – 7 are "1"s du	uring an internal write cycle.

Table 7. Read Status Register Bit Definition

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25128/256 is divided into four array segments. Top quarter (1/4), top half (1/2), or all of the memory segments can be protected. Any of the data within any selected segment will therefore be READ only. The block write protection levels and corresponding status register control bits are shown in Table 8.

The three bits, BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g. WREN, t_{WC} , RDSR).

	Status Re	gister Bits	Array Addresses Protected	
Level	BP1	BP0	AT25128	AT25256
0	0	0	None	None
1(1/4)	0	1	3000 - 3FFF	6000 - 7FFF
2(1/2)	1	0	2000 - 3FFF	4000 - 7FFF
3(All)	1	1	0000 - 3FFF	0000 - 7FFF

 Table 8.
 Block Write Protect Bits





The WRSR instruction also allows the user to enable or disable the write protect (\overline{WP}) pin through the use of the Write Protect Enable (WPEN) bit. Hardware write protection is enabled when the \overline{WP} pin is low and the WPEN bit is "1". Hardware write protection is disabled when *either* the \overline{WP} pin is high or the WPEN bit is "0." When the device is hardware write protected, writes to the Status Register, including the Block Protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory which are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to "0", as long as the \overline{WP} pin is held low.

WPEN	WP	WEN	Protected Blocks	Unprotected Blocks	Status Register
0	Х	0	Protected	Protected	Protected
0	х	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
Х	High	0	Protected	Protected	Protected
Х	High	1	Protected	Writable	Writable

Table 9. WPEN Operation

READ SEQUENCE (READ): Reading the AT25128/256 via the SO pin requires the following sequence. After the \overline{CS} line is pulled low to select a device, the READ op-code is transmitted via the SI line followed by the byte address to be read (see Table 10 on page 9). Upon completion, any data on the SI line will be ignored. The data (D7 – D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the \overline{CS} line should be driven high after the data comes out. The read sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous read cycle.

WRITE SEQUENCE (WRITE): In order to program the AT25128/256, two separate instructions must be executed. First, the device *must be write enabled* via the WREN instruction. Then a Write instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block write protection level. During an internal write cycle, all commands will be ignored except the RDSR instruction.

A Write instruction requires the following sequence. After the \overline{CS} line is pulled low to select the device, the Write op-code is transmitted via the SI line followed by the byte address and the data (D7 – D0) to be programmed (see Table 10 on page 9). Programming will start after the \overline{CS} pin is brought high. The low-to-high transition of the \overline{CS} pin must occur during the SCK low time immediately after clocking in the D0 (LSB) data bit.

The Ready/Busy status of the device can be determined by initiating a Read Status Register (RDSR) instruction. If Bit 0 = "1", the write cycle is still in progress. If Bit 0 = "0", the write cycle has ended. Only the RDSR instruction is enabled during the write programming cycle.

The AT25128/256 is capable of a 64-byte page write operation. After each byte of data is received, the six-low order address bits are internally incremented by one; the highorder bits of the address will remain constant. If more than 64 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25128/256 is automatically returned to the write disable state at the completion of a write cycle.

NOTE: If the device is not Write enabled (WREN), the device will ignore the Write instruction and will return to the standby state, when \overline{CS} is brought high. A new CS falling edge is required to reinitiate the serial communication.

Table 10. Address Key

Address	AT25128	AT25256
A _N	A ₁₃ - A ₀	A ₁₄ - A ₀
Don't Care Bits	A ₁₅ - A ₁₄	A ₁₅

Timing Diagrams (for SPI Mode 0 (0, 0))

Figure 3. Synchronous Data Timing

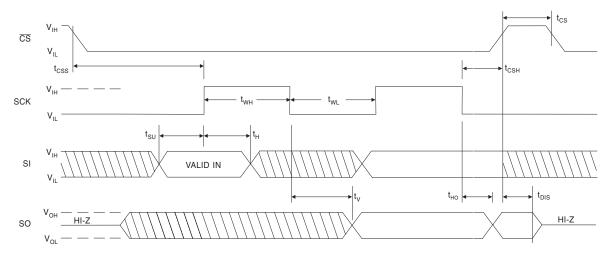






Figure 4. WREN Timing

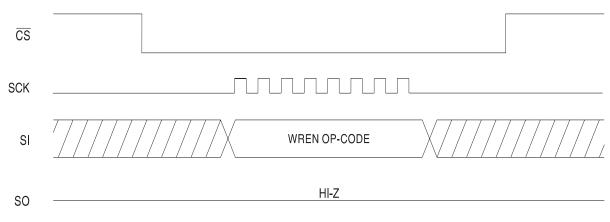
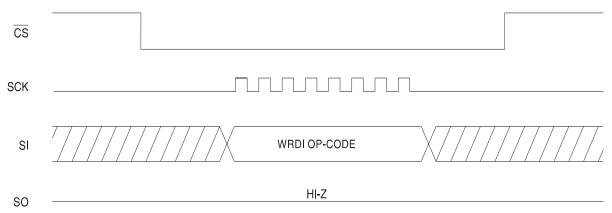


Figure 5. WRDI Timing





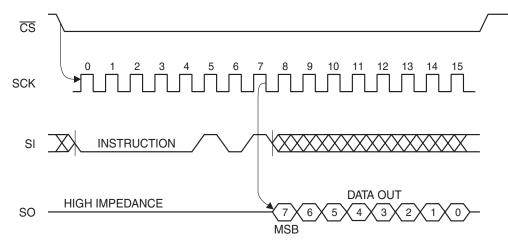


Figure 7. WRSR Timing

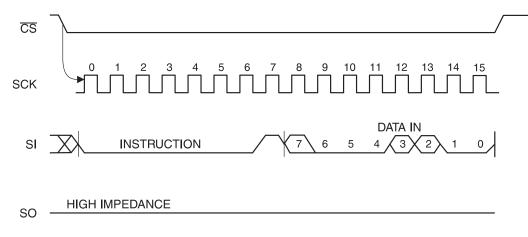


Figure 8. READ Timing

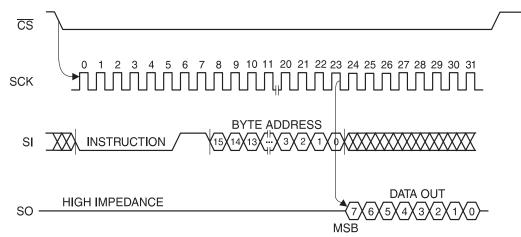


Figure 9. WRITE Timing

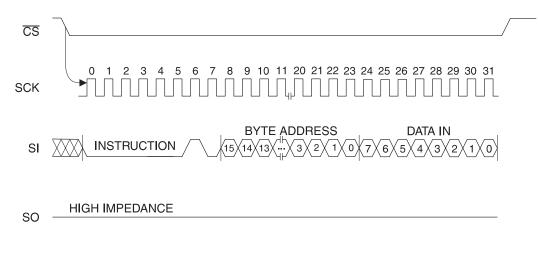
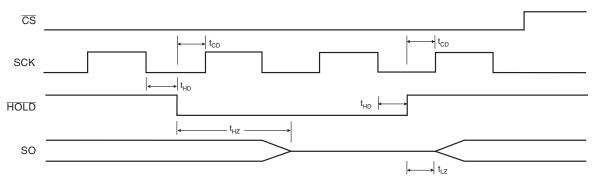




Figure 10. HOLD Timing



AT25128⁽¹⁾ Ordering Information

Ordering Code ⁽²⁾	Package	Operation Range
AT25128-10PI-2.7	8P3	Industrial Temperature (-40°C to 85°C)
AT25128N-10SI-2.7	8S1	
AT25128W-10SI-2.7	8S2	
AT25128N1-10SI-2.7	16S1	
AT25128T1-10TI-2.7	14A2	
AT25128-10PI-1.8	8P3	Industrial Temperature (-40°C to 85°C)
AT25128N-10SI-1.8	8S1	
AT25128W-10SI-1.8	8S2	
AT25128N1-10SI-1.8	16S1	
AT25128T1-10TI-1.8	14A2	
AT25128N-10SJ-2.7	8S1	Lead-Free/Industrial Temperature
AT25128N-10SJ-1.8	8S1	(–40°C to 85°C)
AT25128N-10SE-2.7	8S1	High Grade/Extended Temperature (-40°C to 125°C)

Notes: 1. This device is not recommended for new designs. Please refer to AT25128A.

2. For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC Characteristics tables.

Package Type		
8P3	8-lead, 0.300" Wide, Plastic Dual In-line Package (PDIP)	
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline Package (JEDEC SOIC)	
8S2	8-lead, 0.200" Wide, Plastic Gull Wing Small Outline Package (EIAJ SOIC)	
16S1	16-lead, 0.150" Wide, Plastic Gull Wing Small Outline Package (JEDEC SOIC)	
14A2	14-lead, 0.170" Wide, Thin Shrink Small Outline Package (TSSOP)	
Options		
-2.7	Low-voltage (2.7V to 5.5V)	
-1.8	Low-voltage (1.8V to 5.5V)	





AT25256⁽¹⁾ Ordering Information

Ordering Code ⁽²⁾	Package	Operation Range
AT25256-10PI-2.7	8P3	
AT25256W-10SI-2.7	8S2	Industrial Temperature
AT25256-10CI-2.7	8CN3	(–40°C to 85°C)
AT25256T2-10TI-2.7	20A2	
AT25256-10PI-1.8	8P3	
AT25256W-10SI-1.8	8S2	Industrial Temperature
AT25256-10CI-1.8	8CN3	(–40°C to 85°C)
AT25256T2-10TI-1.8	20A2	
AT25256W-10SJ-2.7	8S2	Lead-Free/Industrial Temperature
AT25256W-10SJ-1.8	8S2	(−40°C to 85°C)
AT25256W-10SE-2.7	8S2	High Grade/Extended Temperature
	652	(–40°C to 125°C)

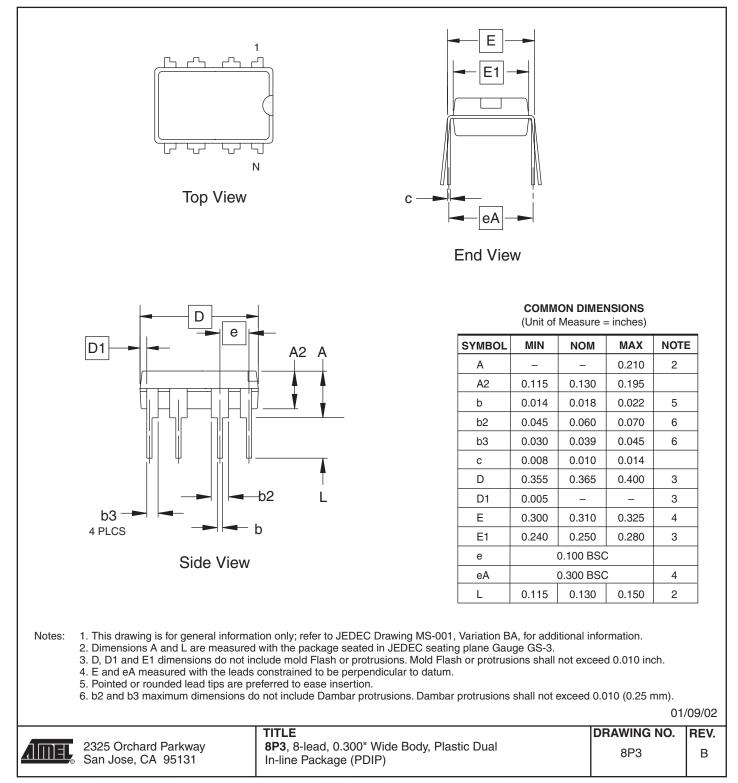
Notes: 1. This device is not recommended for new designs. Please refer to AT25256A.

2. For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC Characteristics tables.

Package Type		
8P3	8-lead, 0.300" Wide, Plastic Dual In-line Package (PDIP)	
8S2	8-lead, 0.200" Wide, Plastic Gull Wing Small Outline Package (EIAJ SOIC)	
8CN3	8-lead, 0.230" Wide, Leadless Array Package (LAP)	
20A2	20-lead, 0.170" Wide, Thin Shrink Small Outline Package (TSSOP)	
Options		
-2.7	Low-voltage (2.7V to 5.5V)	
-1.8	Low-voltage (1.8V to 5.5V)	

Packaging Information

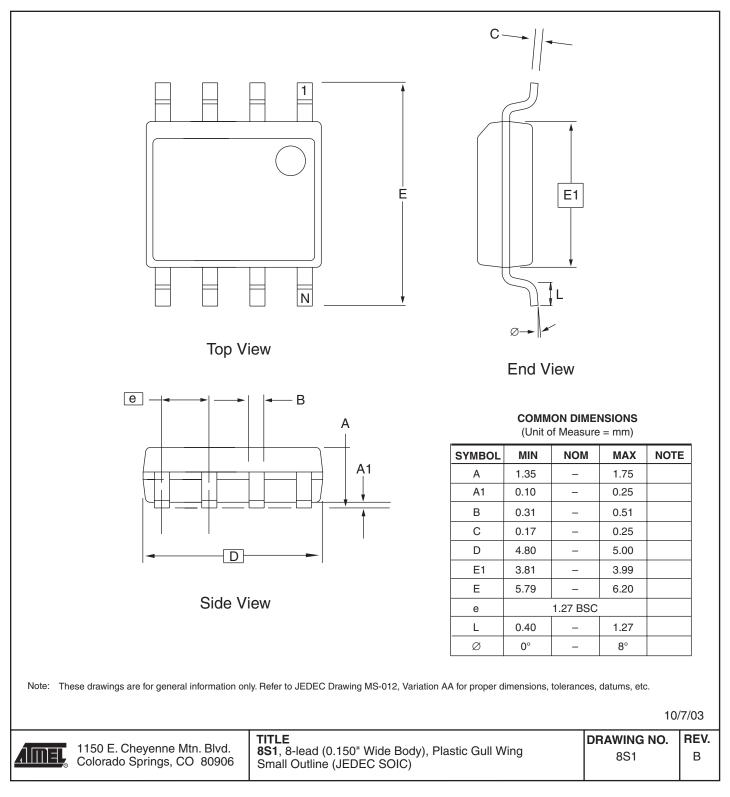
8P3 – PDIP





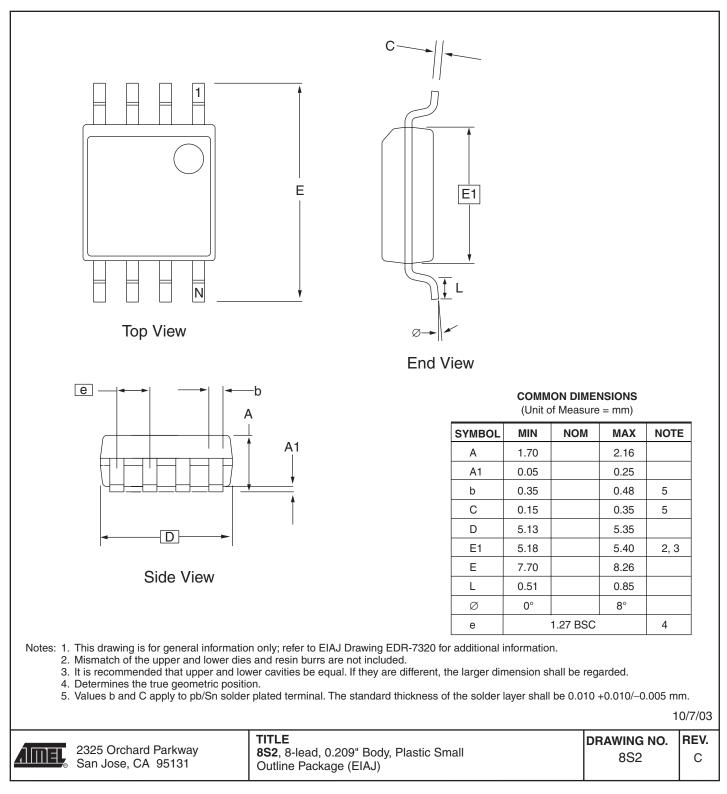


8S1 – JEDEC SOIC



AT25128/256

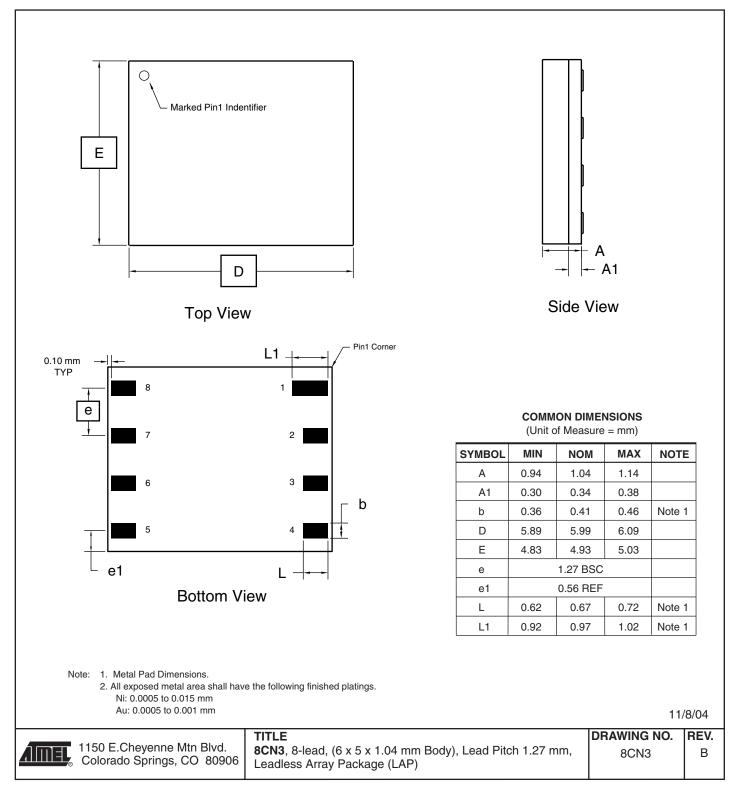
8S2 - EIAJ SOIC





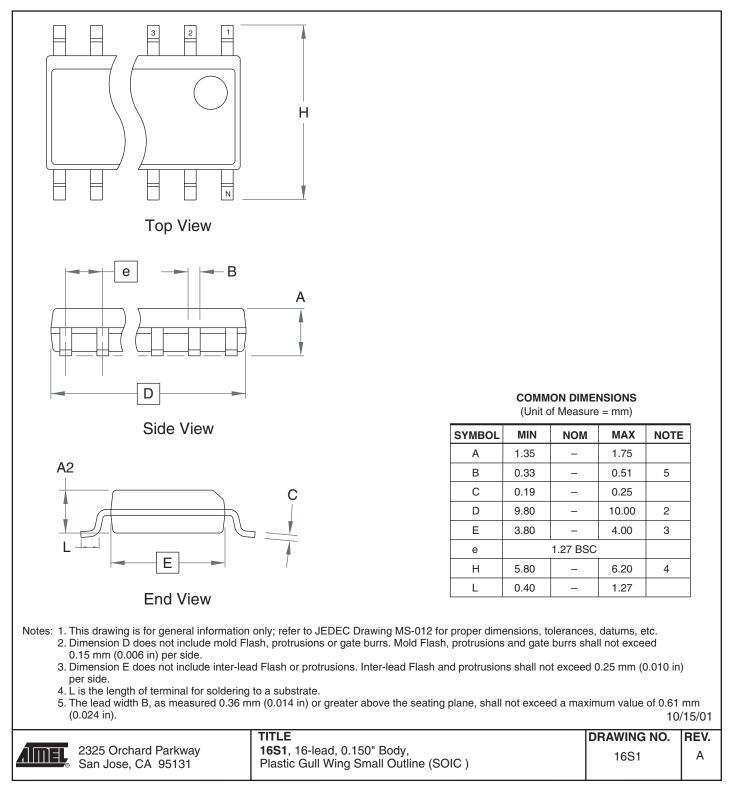


8CN3 – LAP



AT25128/256

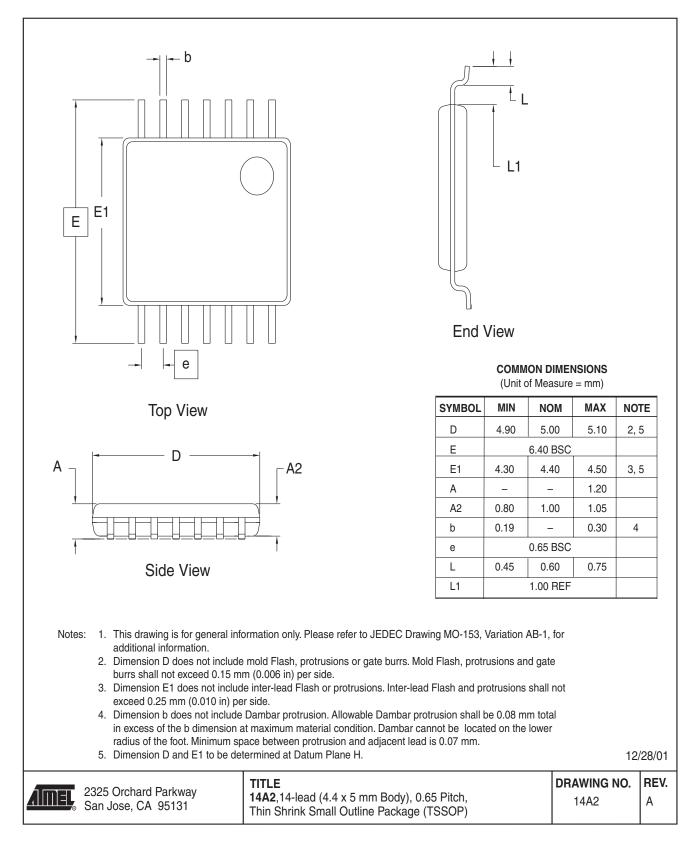
16S1 - JEDEC SOIC







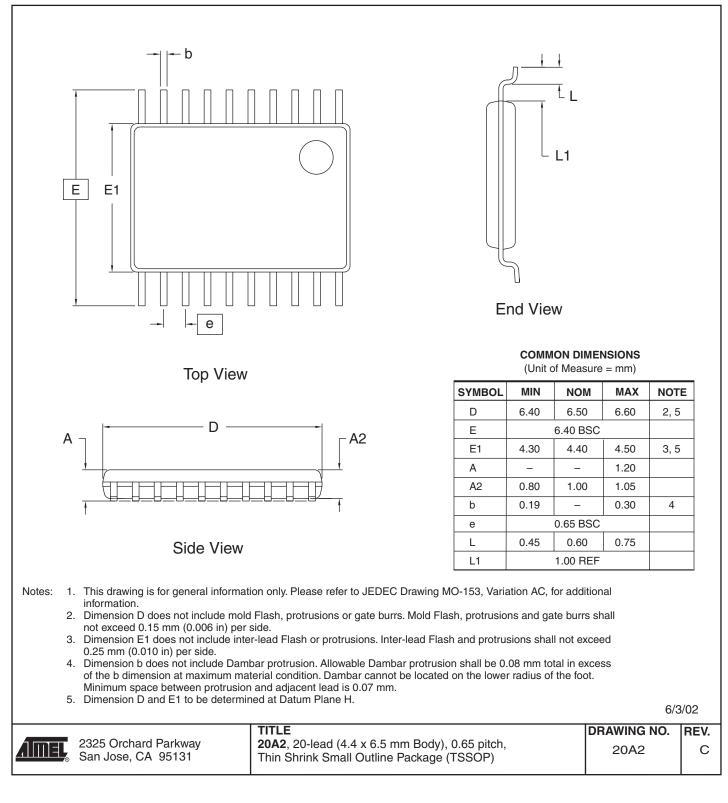
14A2 – TSSOP



²⁰ AT25128/256

AT25128/256

20A2 - TSSOP







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